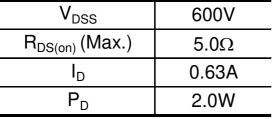


# **ZDS020N60**

#### Nch 600V 0.63A Power MOSFET

Datasheet

V <sub>DSS</sub>	600V
R <sub>DS(on)</sub> (Max.)	5.0Ω
I <sub>D</sub>	0.63A
$P_D$	2.0W



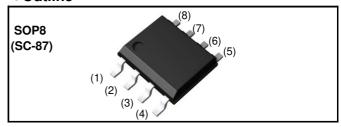
#### Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Gate-source voltage ( $V_{GSS}$ ) guaranteed to be  $\pm 30V$ .
- 4) Drive circuits can be simple.
- 5) Parallel use is easy.
- 6) Pb-free lead plating; RoHS compliant

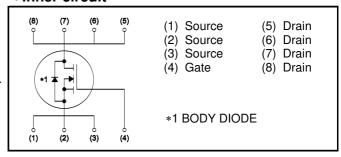
### Application

Switching Power Supply

#### Outline



#### ●Inner circuit



Packaging specifications

	Packaging	Taping
	Reel size (mm)	330
Tuno	Tape width (mm)	12
Туре	Basic ordering unit (pcs)	2,500
	Taping code	TB
	Marking	ZDS020N60

### •Absolute maximum ratings( $T_a = 25$ °C)

Parameter	Symbol	Value	Unit
Drain - Source voltage	$V_{ extsf{DSS}}$	600	V
Continuous drain current $T_c = 25$ °C	I <sub>D</sub> <sup>*1</sup>	±0.63	А
Pulsed drain current	I <sub>D,pulse</sub> *2	±2.5	А
Gate - Source voltage	$V_{GSS}$	±30	V
Power dissipation (T <sub>c</sub> = 25°C)	P <sub>D</sub>	2.0	W
Junction temperature	T <sub>j</sub>	150	°C
Range of storage temperature	T <sub>stg</sub>	-55 to +150	°C

#### ●Thermal resistance

Parameter	Symbol	Values			Unit
raiametei	Зуппоп	Min.	Тур.	Max.	Offic
Thermal resistance, junction - ambient	$R_{thJA}$	-	-	62.5	°C/W

# • Electrical characteristics $(T_a = 25^{\circ}C)$

Parameter	Symbol	Conditions	Values			Unit
r arameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V$ , $I_D = 1mA$	600	ı	-	V
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{DS} = 600V, V_{GS} = 0V$	-		100	μΑ
Gate - Source leakage current	I <sub>GSS</sub>	$V_{GS} = \pm 30V, V_{DS} = 0V$	-	-	±100	nA
Gate threshold voltage	V <sub>GS (th)</sub>	$V_{DS} = 10V$ , $I_D = 1mA$	2.0	-	4.0	V
Static drain - source on - state resistance	R <sub>DS(on)</sub> *3	$V_{GS} = 10V, I_D = 0.5A$	-	4.4	5.0	Ω

## $\bullet \textbf{Electrical characteristics}(T_a = 25^{\circ}C)$

Parameter	Symbol	Conditions	Values			Unit
raiametei	Symbol	Conditions	Min.	Тур.	Max.	Offic
Transconductance	g <sub>fs</sub> *3	$V_{DS} = 10V, I_D = 0.5A$	0.05	0.5	-	S
Input capacitance	C <sub>iss</sub>	$V_{GS} = 0V$	-	310	-	
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 10V	-	145	-	рF
Reverse transfer capacitance	$C_{rss}$	f = 1MHz	-	40	-	
Turn - on delay time	t <sub>d(on)</sub> *3	$V_{DD} \simeq 200V, V_{GS} = 10V$	-	25	-	
Rise time	t <sub>r</sub> *3	$I_D = 600 \text{mA}$	-	20	-	ne
Turn - off delay time	t <sub>d(off)</sub> *3	$R_L = 333\Omega$	-	65	-	ns
Fall time	t <sub>f</sub> *3	$R_G = 50\Omega$	-	65	-	

## ullet Gate Charge characteristics(T<sub>a</sub> = 25°C)

Parameter	Symbol	Conditions	Values			Unit
raiametei	Symbol	Conditions	Min.	Тур.	Max.	Offic
Total gate charge	$Q_g^{*3}$	$V_{DD} \simeq 450V$	-	12	20	
Gate - Source charge	Q <sub>gs</sub> *3	$I_D = 600 \text{mA}$	-	3	-	nC
Gate - Drain charge	Q <sub>gd</sub> *3	V <sub>GS</sub> = 10V	-	5	1	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} \simeq 450V$ , $I_D = 600$ mA	ı	5	-	V

<sup>\*1</sup> Limited only by maximum temperature allowed.

<sup>\*2</sup> Pw  $\leq$  10 $\mu$ s, Duty cycle  $\leq$  1%

<sup>\*3</sup> Pulsed

## ullet Body diode electrical characteristics (Source-Drain)(T<sub>a</sub> = 25°C)

Parameter	Symbol	Conditions	Values			Unit
Farameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Inverse diode continuous, forward current	l <sub>S</sub> *1	T <sub>c</sub> = 25°C	-	ı	0.63	А
Inverse diode direct current, pulsed	I <sub>SM</sub> *2	11 <sub>c</sub> = 25 0	-	-	2.5	Α
Forward voltage	V <sub>SD</sub> *3	$V_{GS} = 0V, I_{S} = 1A$	-	-	1.5	V

Fig.1 Power Dissipation Derating Curve

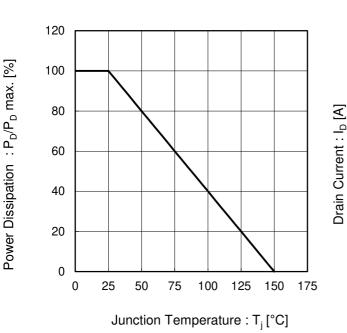
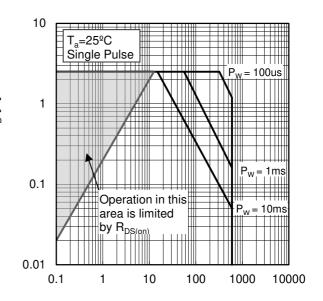
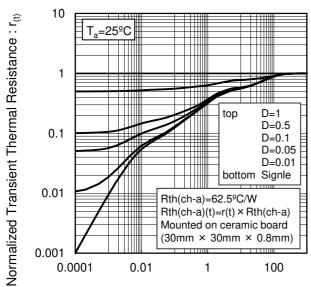


Fig.2 Maximum Safe Operating Area



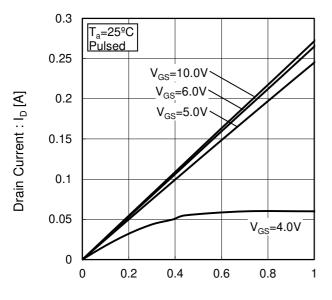
Drain - Source Voltage :  $V_{DS}[V]$ 

Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width



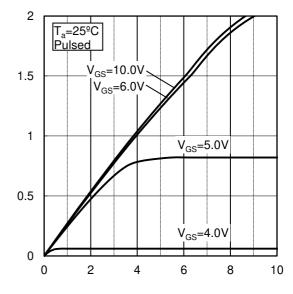
Pulse Width: Pw[s]

Fig.4 Typical Output Characteristics(I)



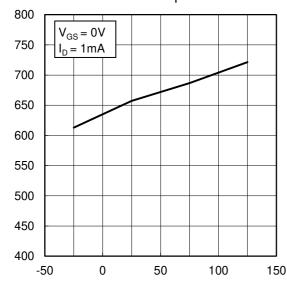
Drain - Source Voltage : V<sub>DS</sub> [V]

Fig.5 Typical Output Characteristics(II)



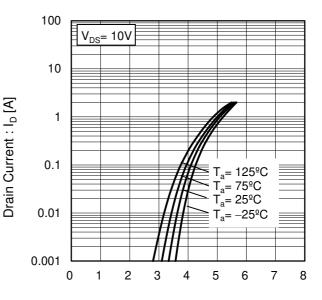
Drain - Source Voltage : V<sub>DS</sub> [V]

Fig.6 Breakdown Voltage vs. Channel Temperature



Junction Temperature : T<sub>i</sub> [°C]

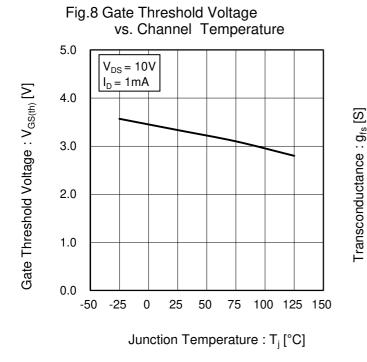
Fig.7 Typical Transfer Characteristics



Gate - Source Voltage : V<sub>GS</sub> [V]

Drain - Source Breakdown Voltage :  $V_{(BR)DSS}\left[V\right]$ 

Drain Current : I<sub>D</sub> [A]



100 V<sub>DS</sub>= 10V 10 1 T<sub>a</sub>= -25°C T<sub>a</sub>=25°C T<sub>a</sub>=75°C T<sub>a</sub>=125°C

1

Drain Current : I<sub>D</sub> [A]

10

100

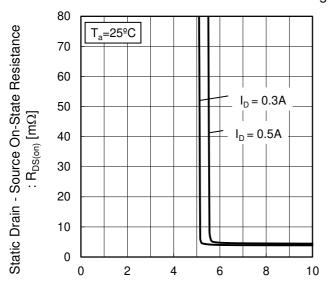
0.01

0.01

0.1

Fig.9 Transconductance vs. Drain Current

Fig.10 Static Drain - Source On - State Resistance vs. Gate Source Voltage



Gate - Source Voltage :  $V_{GS}[V]$ 

Fig.11 Static Drain - Source On - State Resistance vs. Drain Current(II)

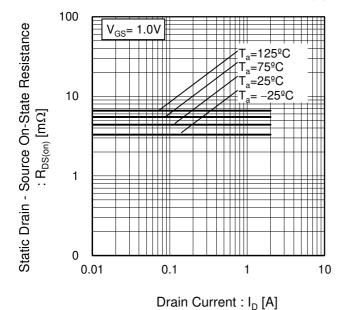
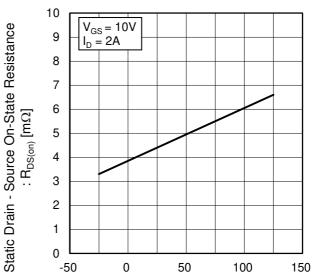
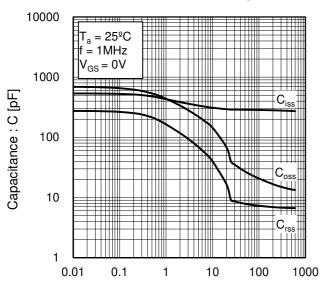


Fig.12 Static Drain - Source On - State Resistance vs. Junction Temperature



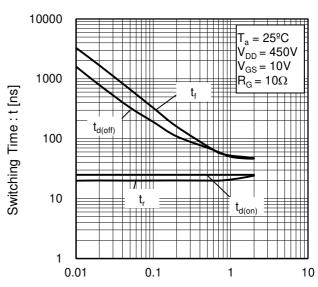
Junction Temperature : T<sub>i</sub> [°C]

Fig.13 Typical Capacitance vs. Drain - Source Voltage



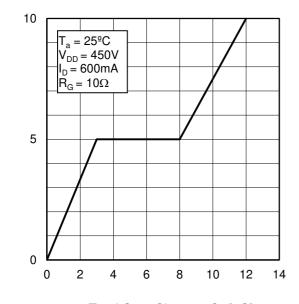
Drain - Source Voltage : V<sub>DS</sub> [V]

Fig.14 Switching Characteristics



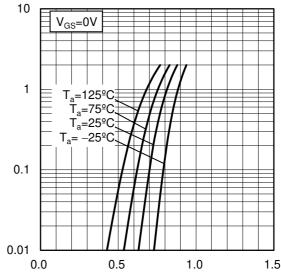
Drain Current : I<sub>D</sub> [A]

Fig.15 Dynamic Input Characteristics



Total Gate Charge : Q<sub>g</sub> [nC]

Fig.16 Inverse Diode Forward Current vs. Source - Drain Voltage



Source - Drain Voltage : V<sub>SD</sub> [V]

Gate - Source Voltage : V<sub>GS</sub> [V]

Inverse Diode Forward Current : I<sub>S</sub> [A]

#### Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

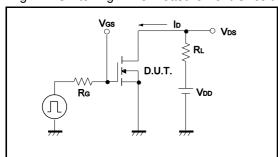


Fig.2-1 Gate Charge Measurement Circuit

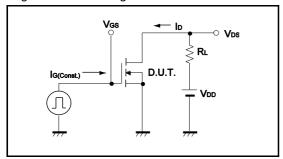


Fig.1-2 Switching Waveforms

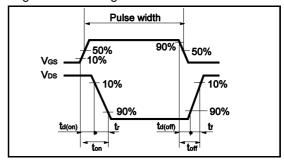
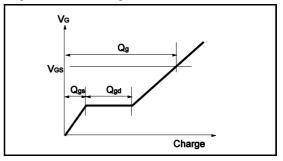
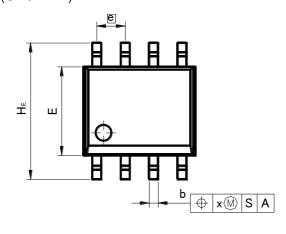


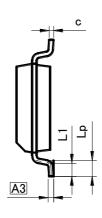
Fig.2-2 Gate Charge Waveform

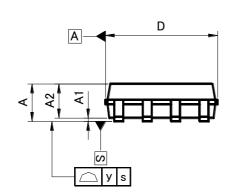


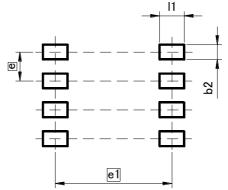
### ●Dimensions (Unit:mm)











### Patterm of terminal position areas

DIM	MILIM	ETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	_	1.75	_	0.069
A1	0.	15	0.0	006
A2	1.40	1.60	0.055	0.063
A3	0.3	25	0.	01
b	0.30	0.50	0.012	0.02
С	0.10	0.30	0.004	0.012
D	4.80	5.20	0.189	0.205
E	3.75	4.05	0.148	0.159
е	1.27		0.	05
HE	5.70	6.30	0.224	0.248
L1	0.50	0.70	0.02	0.028
Lp	0.65	0.85	0.026	0.033
х	0.15		0.0	006
У	0.10		.10 0.004	

DIM	MILIMETERS		INCHES		
DIIVI	MIN	MAX MIN		MAX	
b2	_	0.65	- 0.026		
e1	5.	15	0.2	:03	
11	_	1.15	_	0.045	

Dimension in mm/inches

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